

# MJ N-Channel Enhancement Mode Power MOSFET

## Description

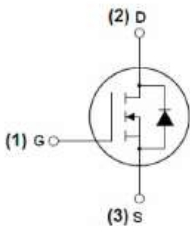
The MJ30H12K uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

## General Features

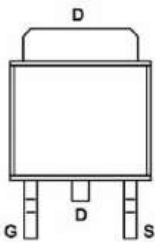
- ◆  $V_{DS} = 30V, I_D = 120A$   
 $R_{DS(ON)} < 4.5m\Omega @ V_{GS} = 10V$  (Typ:3.5m $\Omega$ )
- ◆ High density cell design for ultra low  $R_{dson}$
- ◆ Fully characterized avalanche voltage and current
- ◆ Good stability and uniformity with high  $E_{AS}$
- ◆ Excellent package for good heat dissipation
- ◆ Special process technology for high ESD capability

## Application

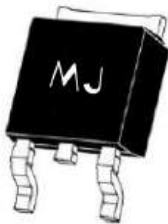
- ◆ Power switching application
- ◆ Hard switched and high frequency circuits
- ◆ Uninterruptible power supply



Schematic diagram



Marking and pin assignment



TO-252-2L top view

100% UIS TESTED! 100%  $\Delta V_{ds}$  TESTED!

## Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
MJ30H12K	MJ30H12K	TO-252-2L	-	-	-

## Absolute Maximum Ratings (T<sub>A</sub> =25 °Cunless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	±20	V
Drain Current-Continuous	$I_D$	120	A
Drain Current-Continuous(T <sub>C</sub> =100°C)	$I_{D(100^{\circ}C)}$	84	A
Pulsed Drain Current	$I_{DM}$	400	A
Maximum Power Dissipation	$P_D$	120	W
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	350	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	°C

## Thermal Characteristic

Thermal Resistance,Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	1.25	°C/W
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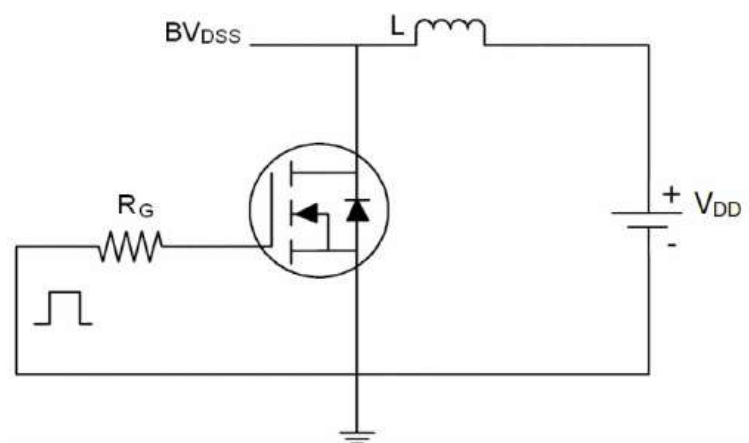
Electrical Characteristics (T<sub>A</sub> =25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =±20V,V <sub>GS</sub> =0V	-	-	±100	nA
On Characteristics <small>(Note 3)</small>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	1	1.6	3	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	3.5	4.5	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =10V,I <sub>D</sub> =20A	50	-	-	S
Dynamic Characteristics <small>(Note 4)</small>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V,V <sub>GS</sub> =0V F=1.0MHz	-	4120	-	PF
Output Capacitance	C <sub>Oss</sub>		-	498	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	456	-	PF
Switching Characteristics <small>(Note 4)</small>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> =10V,V <sub>DS</sub> =20V R <sub>L</sub> =0.75Ω,R <sub>GEN</sub> =3Ω	-	11	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	10	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	38	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	11	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =10V,V <sub>DS</sub> =15V I <sub>D</sub> =20A	-	79	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	9	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	18	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage <small>(Note 3)</small>	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =20A	-	-	1.2	V
Diode Forward Current <small>(Note 2)</small>	I <sub>S</sub>		-	-	120	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> =25°C, I <sub>F</sub> =60A di/dt=100A/μs <small>(Note 3)</small>	-	58	-	nS
Reverse Recovery Charge	Q <sub>rr</sub>		-	115	-	nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible(turn-on is dominated by LS+LD)				

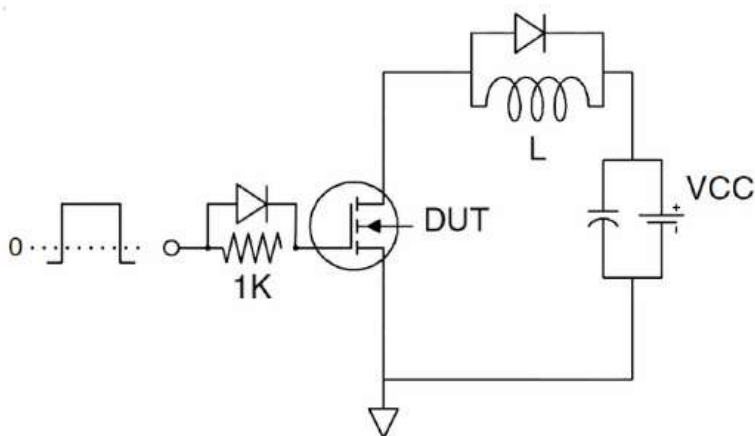
Notes:

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② Surface Mounted on FR4 Board, t ≤ 10 sec.
- ③ Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
- ④ Guaranteed by design, not subject to production
- ⑤ EAS condition: T<sub>J</sub>=25°C,V<sub>DS</sub>=15V,V<sub>G</sub>=10V,L=0.5mH,R<sub>g</sub>=25Ω

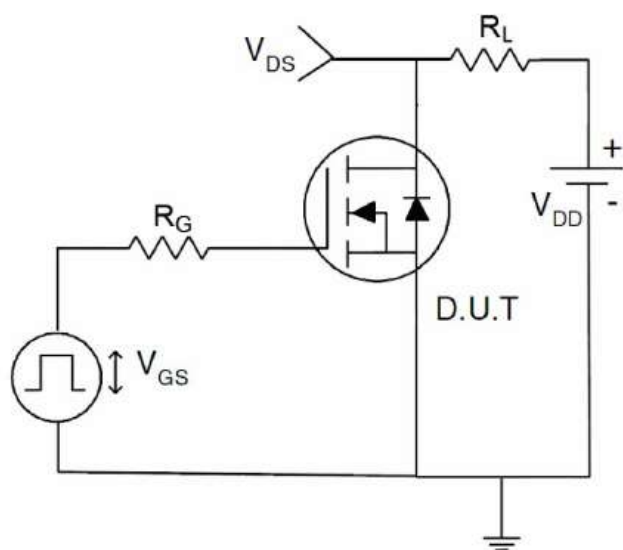
# Test circuit



EAS test Circuit

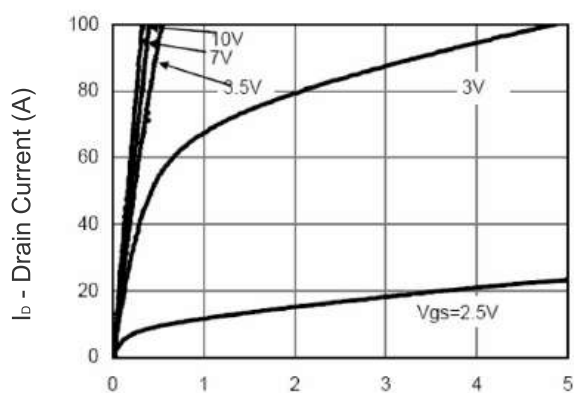


Gate charge test Circuit



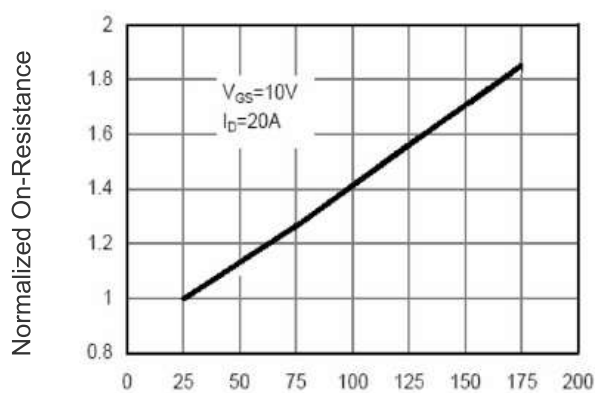
Switch Time Test Circuit

## Typical Electrical and Thermal Characteristics (Curves)



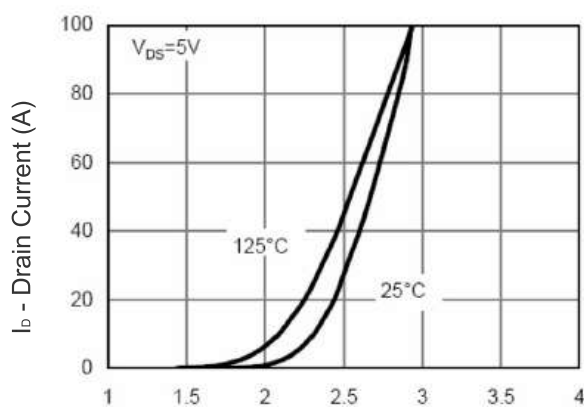
Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



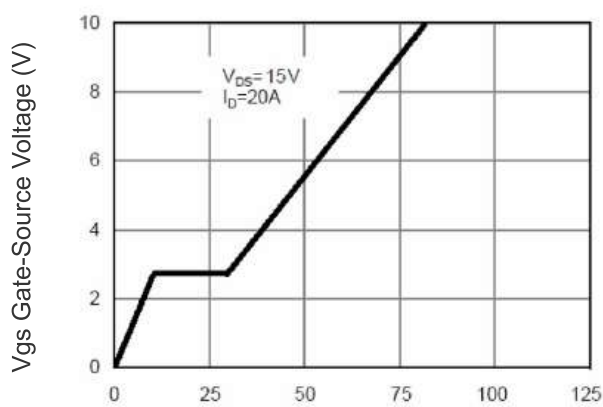
Tj -Junction Temperature(°C)

Figure 4 Rdson-Junction Temperature



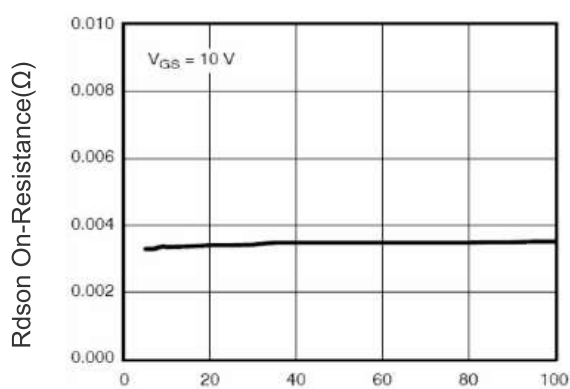
Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics



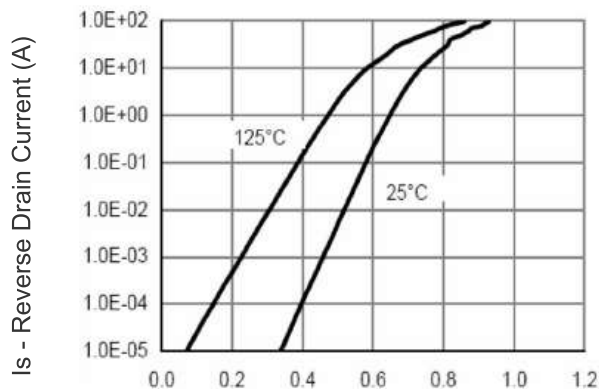
Qg Gate Charge (nC)

Figure 5 Gate Charge



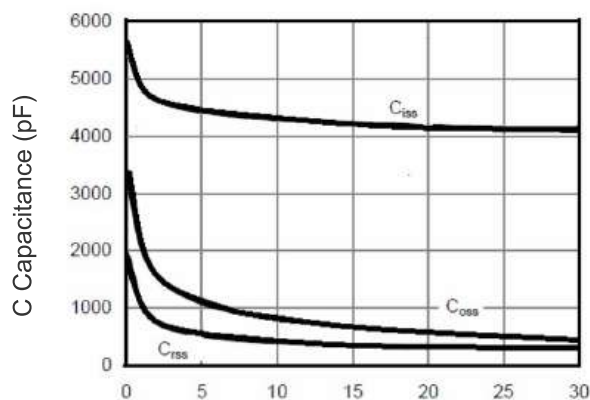
Id - Drain Current (A)

Figure 3 Rdson- Drain Current

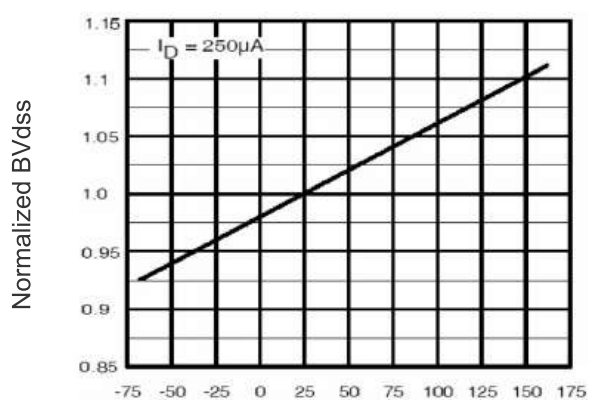


Vsd Source-Drain Voltage (V)

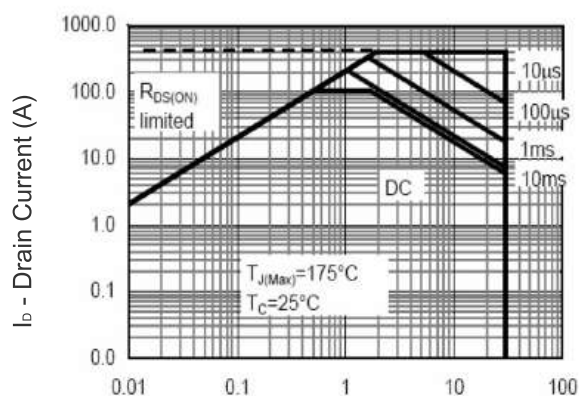
Figure 6 Source- Drain Diode Forward



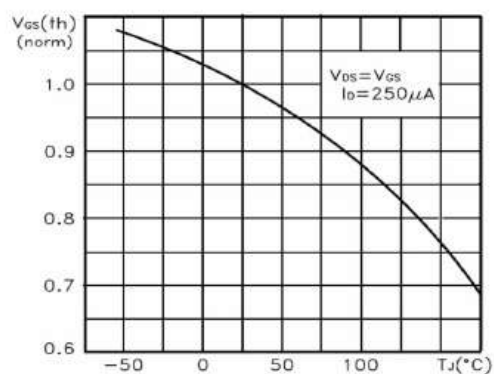
Vds Drain-Source Voltage (V)  
Figure 7 Capacitance vs Vds



Tj -Junction Temperature(°C)  
Figure 9 BV<sub>DSS</sub> vs Junction Temperature



Vds Drain-Source Voltage (V)  
Figure 8 Safe Operation Area



Tj -Junction Temperature(°C)  
Figure 10 V<sub>GS(th)</sub> vs Junction Temperature

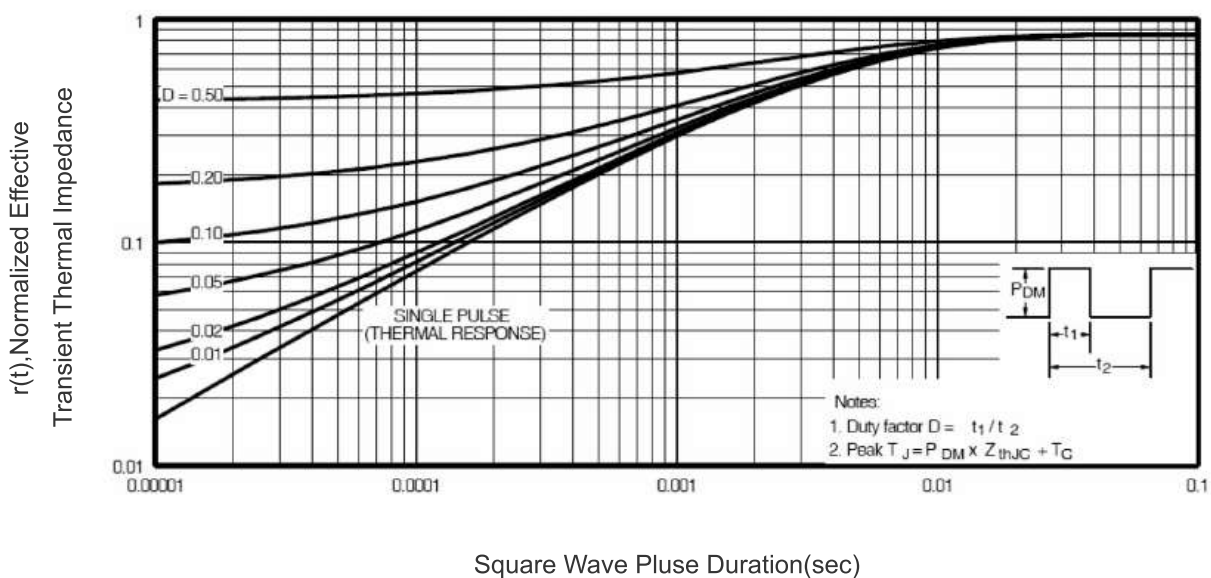
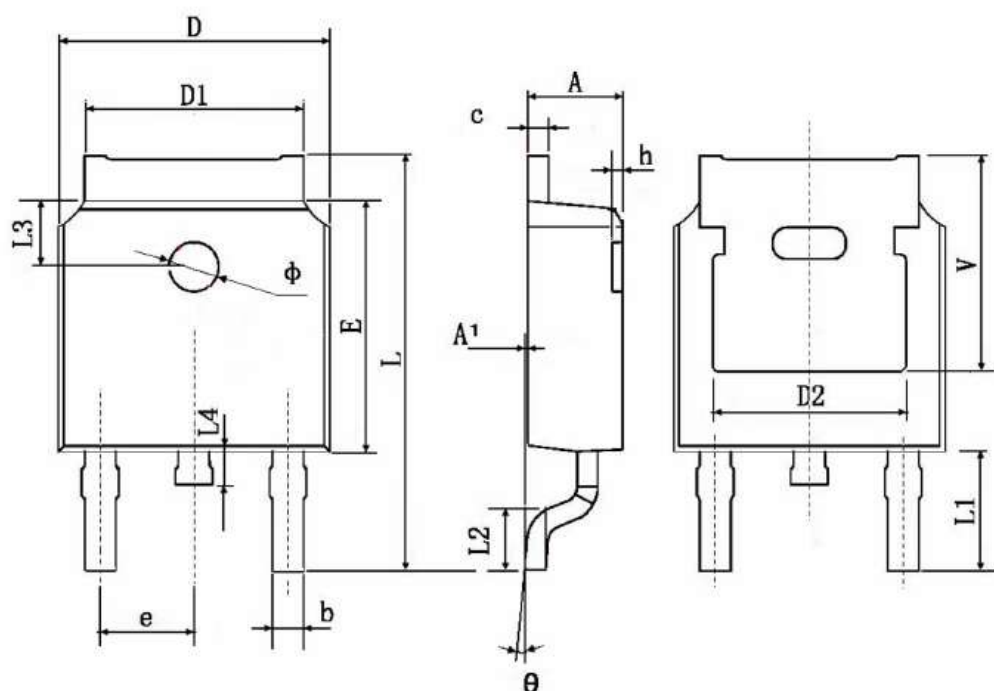


Figure 11 Normalized Maximum Transient Thermal Impedance

# TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

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